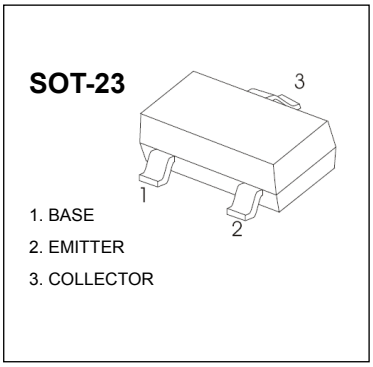
JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO.,LTD

SOT-23 Plastic-Encapsulate Transistors

S8050 TRANSISTOR (NPN)



FEATURES

- Complimentary to S8550
- Collector Current: I_C=0.5A

MARKING: J3Y

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	40	V
V_{CEO}	Collector-Emitter Voltage	25	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	0.5	A
P_C	Collector Dissipation	0.3	W
$R_{\Theta JA}$	Thermal Resistance from Junction to Ambient	417	℃/W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55-150	℃

ELECTRICAL CHARACTERISTICS (T_a=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C= 100μA, I_E=0	40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=1mA, I_B=0	25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=100μA, I_C=0	5			V
Collector cut-off current	I_{CBO}	V_{CB}=40 V , I_E=0			0.1	μA
Collector cut-off current	I_{CEO}	V_{CB}=20V , I_E=0			0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}= 5V , I_C=0			0.1	μA
DC current gain	$h_{FE(1)}$	V_{CE}=1V, I_C= 50mA	120		400	
	$h_{FE(2)}$	V_{CE}=1V, I_C= 500mA	50			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I=500 mA, I_B= 50mA			0.6	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=500 mA, I_B= 50mA			1.2	V
Transition frequency	f_T	V_{CE}=6V, I_C= 20mA f=30MHz	150			MHz

CLASSIFICATION OF $h_{FE(1)}$

Rank	L	H	J
Range	120-200	200-350	300-400

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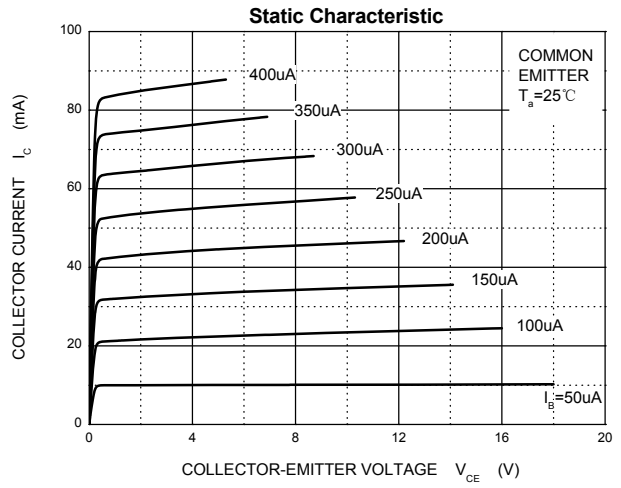
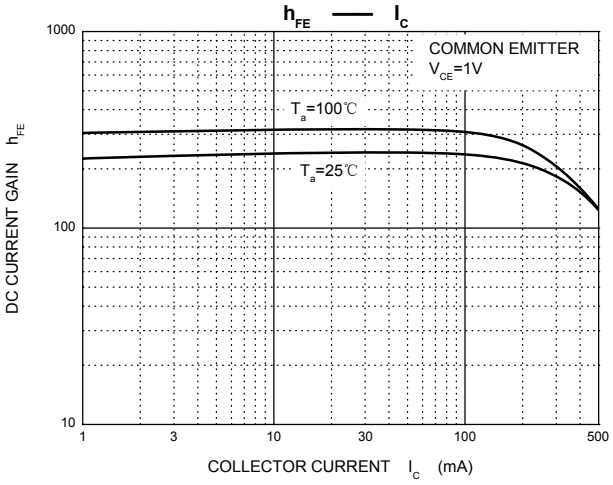
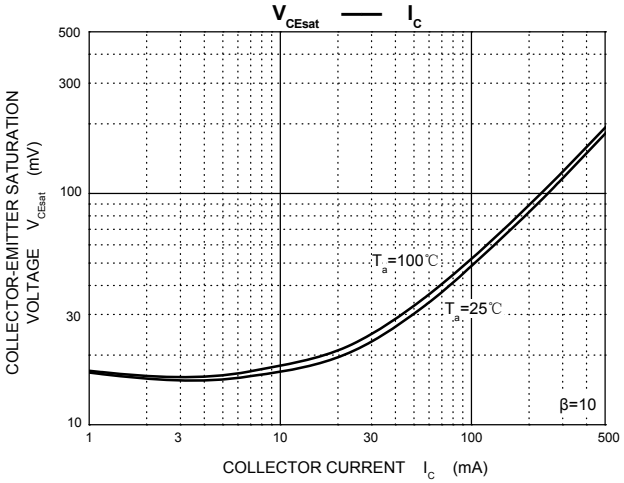
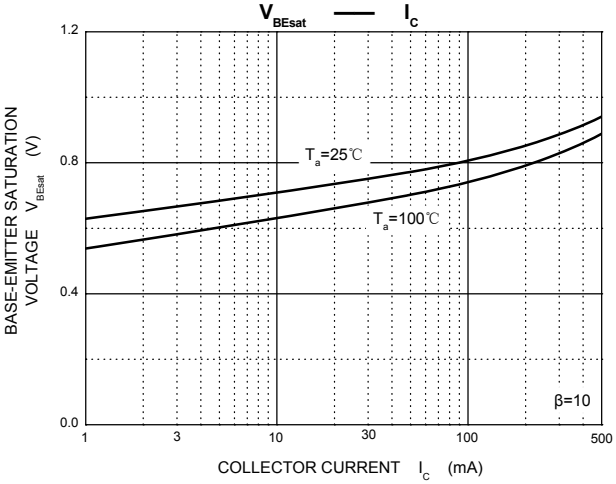
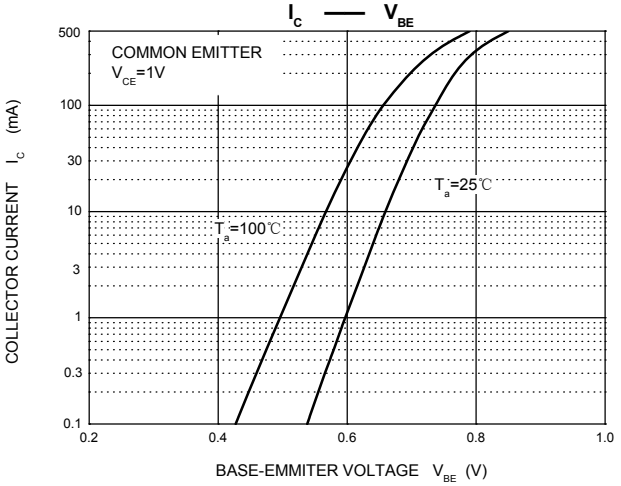
Typical Characterisitics S8050

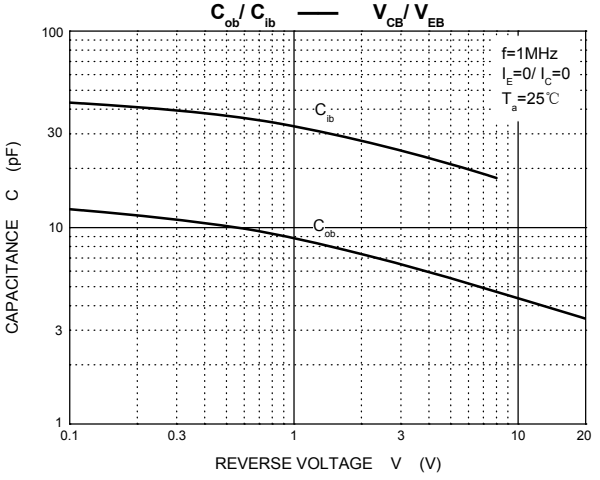


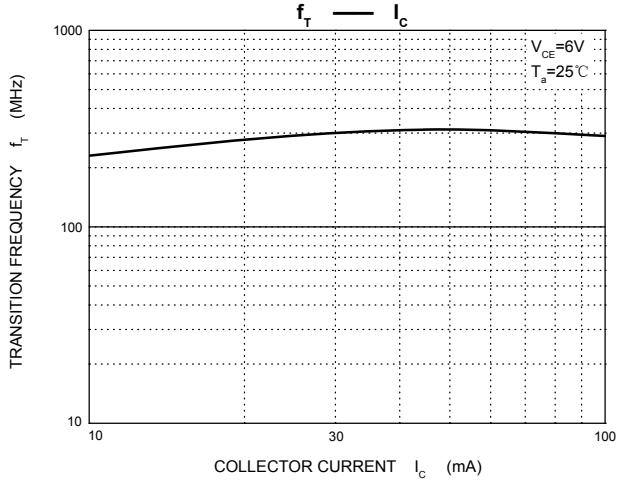


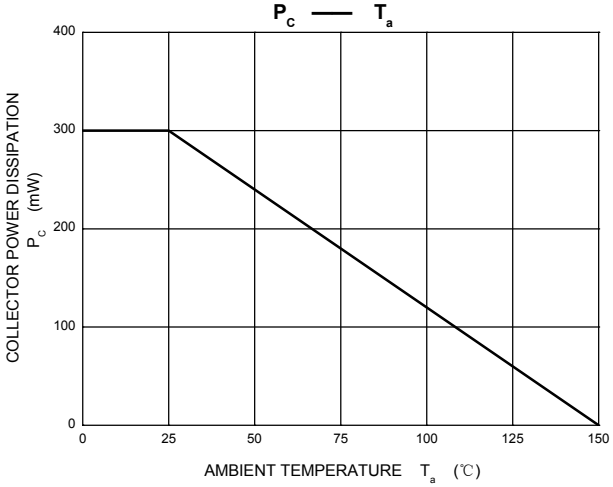












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